Review of: "multilayer graphene and graphene grown on different transistor layers are such forms"

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Although the distance is still on the scale of a few micrometers and the time is still measured in nanoseconds, it essentially opens up the possibility of using rotation in microelectronic components.

The high speed of switching (doping) in the nMOS transistor circuit of Graphene transistor is possible only because it can do p- and n (positive and negative) doping, and graphene doping is a main parameter in the development of nMOS transistor Graphene transistor. The bias voltage is applied to the graphene transistors in such a way that it always operates in its "active" region, that is, the curved or active linear part is used for the output characteristics. Graphene, which consists of only one carbon atom, can be used to create multilayer graphene field-effect transistors that consume less energy and take up less space. Graphene is a semi-conducting material with zero gap and not suitable for logic circuits, but using technology, they create different forms of this material that have different gaps. Graphene strips, multilayer graphene and graphene grown on different transistor layers are such forms. Modeling Si/Cu nanoparticles based on a relationship between molecular mechanics and solid mechanics, an energy-equivalent model is used for the mechanical properties and nanomolecular structure of the sputtering layer of materials, macroscopic properties of nanoparticles such as melting point, boiling point and electrical conductivity. It is done through a sample that is large enough to be measured in normal laboratory conditions. When the melting point of a nanomolecule is measured, in fact, the behavior of a large number of nanoparticle molecules is examined, and this is not true for all materials; When the material size is reduced and reaches nanometer dimensions, completely different behavior and properties may be seen compared to the same material in large dimensions.

In the nano transistor structure, the electronic quantity that is more easily available is the ionization potential, and the ionization potential is greater in the size of the small grains of the nano structure (smaller particles), that is, as the size of the particles increases, their ionization potential decreases. Finds.

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